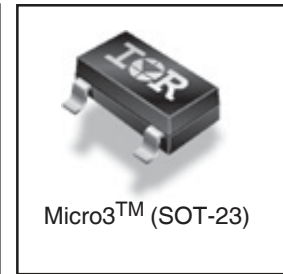
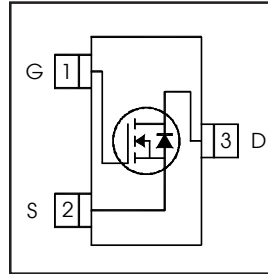


HEXFET® Power MOSFET

V_{DS}	100	V
$R_{DS(on) \text{ max}}$ (@ $V_{GS} = 10V$)	220	m Ω
Q_g (typical)	2.5	nC
I_D (@ $T_A = 25^\circ C$)	1.6	A



Features

Industry-standard pinout SOT-23 Package
Compatible with Existing Surface Mount Techniques
RoHS Compliant, Halogen-Free
MSL1, Industrial qualification



Benefits

Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRLML0100TRPbF-1	Micro3™ (SOT-23)	Tape and Reel	3000	IRLML0100TRPbF-1

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	100	V
I_D @ $T_A = 25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	1.6	A
I_D @ $T_A = 70^\circ C$	Continuous Drain Current, V_{GS} @ 10V	1.3	
I_{DM}	Pulsed Drain Current	7.0	
P_D @ $T_A = 25^\circ C$	Maximum Power Dissipation	1.3	W
P_D @ $T_A = 70^\circ C$	Maximum Power Dissipation	0.8	
	Linear Derating Factor	0.01	
V_{GS}	Gate-to-Source Voltage	± 16	V
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	$^\circ C$

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient ③	—	100	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient (t<10s) ④	—	99	

Electric Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

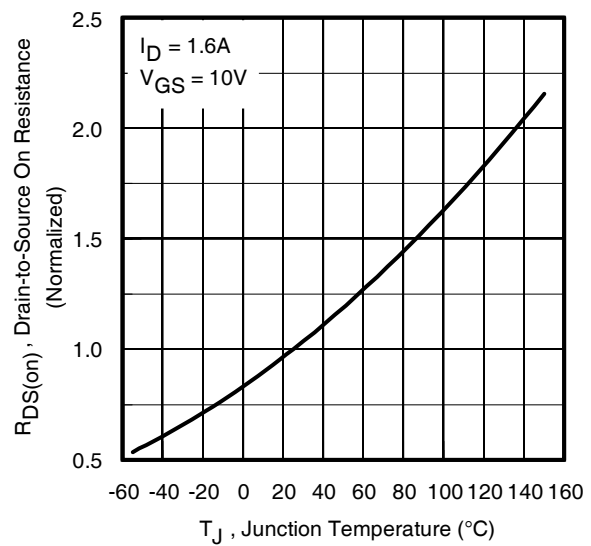
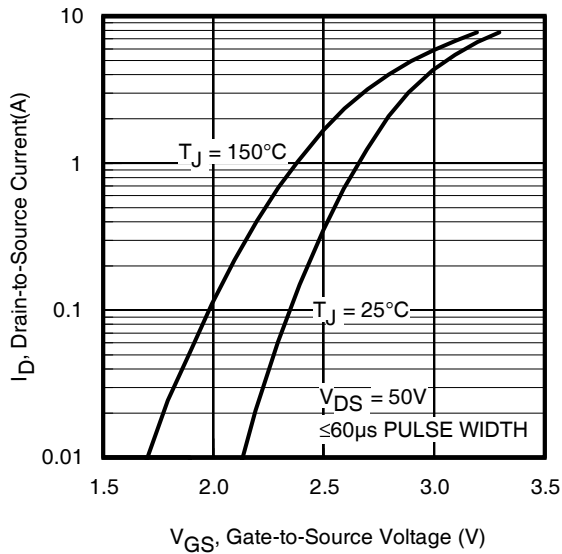
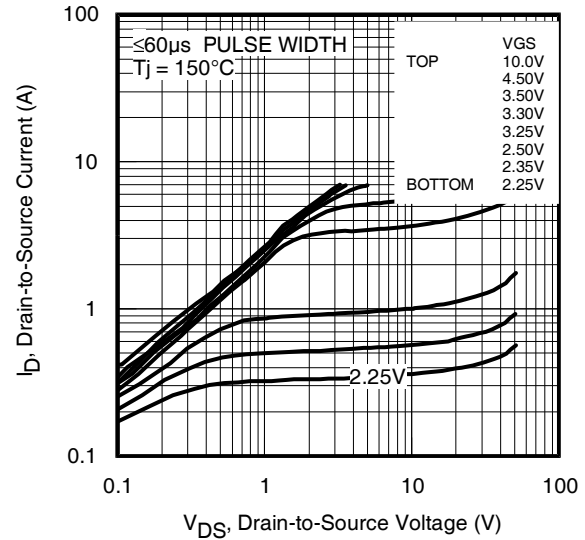
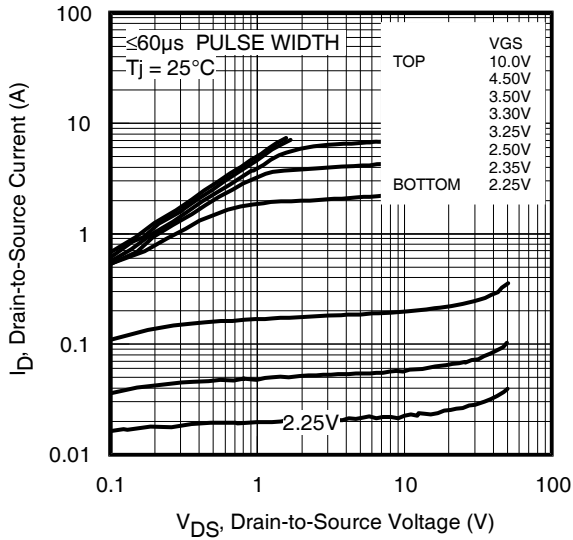
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.10	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	190	235	m Ω	$V_{GS} = 4.5V, I_D = 1.3A$ ②
		—	178	220		$V_{GS} = 10V, I_D = 1.6A$ ②
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.5	V	$V_{DS} = V_{GS}, I_D = 25\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 100V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 100V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -16V$
R_G	Internal Gate Resistance	—	1.3	—	Ω	
g_{fs}	Forward Transconductance	5.7	—	—	S	$V_{DS} = 50V, I_D = 1.6A$
Q_g	Total Gate Charge	—	2.5	—	nC	$I_D = 1.6A$
Q_{gs}	Gate-to-Source Charge	—	0.5	—		$V_{DS} = 50V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	1.2	—		$V_{GS} = 4.5V$ ②
$t_{d(on)}$	Turn-On Delay Time	—	2.2	—	ns	$V_{DD} = 50V$ ②
t_r	Rise Time	—	2.1	—		$I_D = 1.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	9.0	—		$R_G = 6.8\Omega$
t_f	Fall Time	—	3.6	—		$V_{GS} = 4.5V$
C_{iss}	Input Capacitance	—	290	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	27	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	13	—		$f = 1.0MHz$

Source - Drain Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	1.1	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	7.0		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 1.1A, V_{GS} = 0V$ ②
t_{rr}	Reverse Recovery Time	—	20	30	ns	$T_J = 25^\circ\text{C}, V_R = 50V, I_F = 1.1A$
Q_{rr}	Reverse Recovery Charge	—	13	20	nC	$di/dt = 100A/\mu s$ ②

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ③ Surface mounted on 1 in square Cu board
- ④ Refer to [application note #AN-994](#).



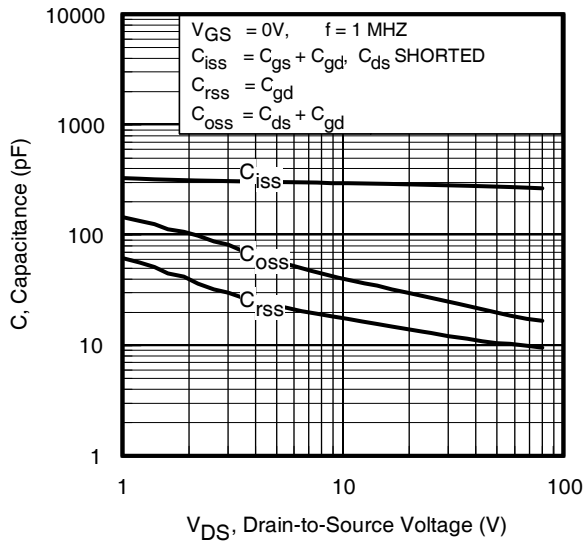


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

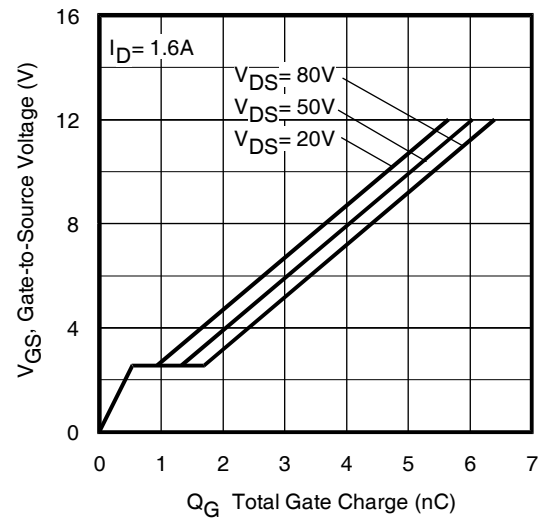


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

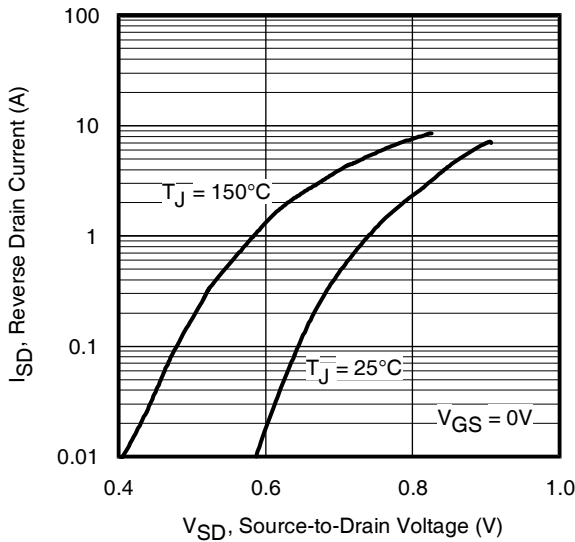


Fig 7. Typical Source-Drain Diode Forward Voltage

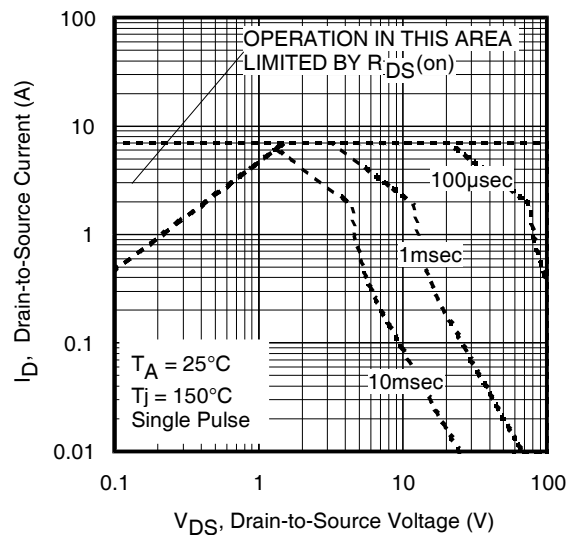


Fig 8. Maximum Safe Operating Area

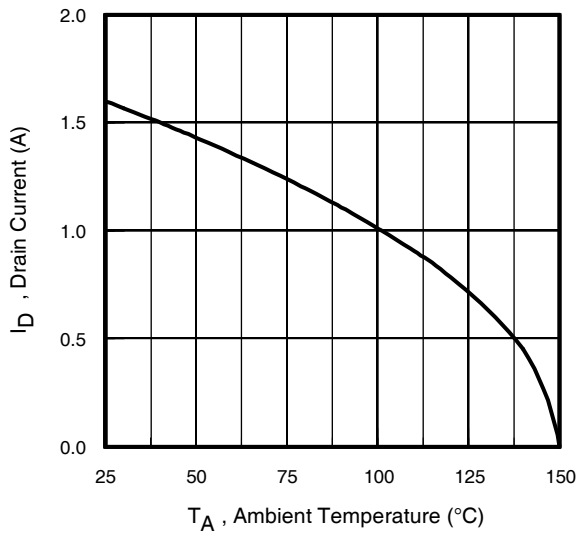


Fig 9. Maximum Drain Current Vs. Ambient Temperature

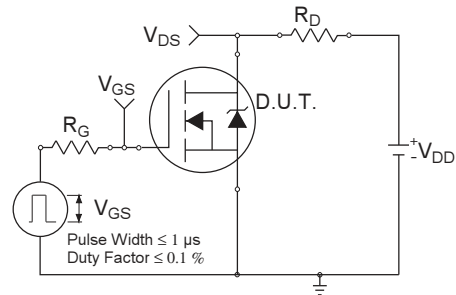


Fig 10a. Switching Time Test Circuit

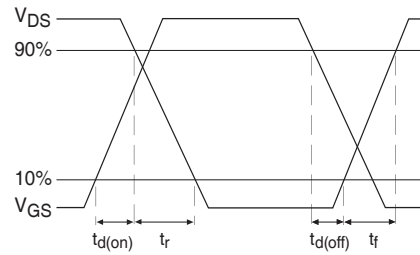


Fig 10b. Switching Time Waveforms

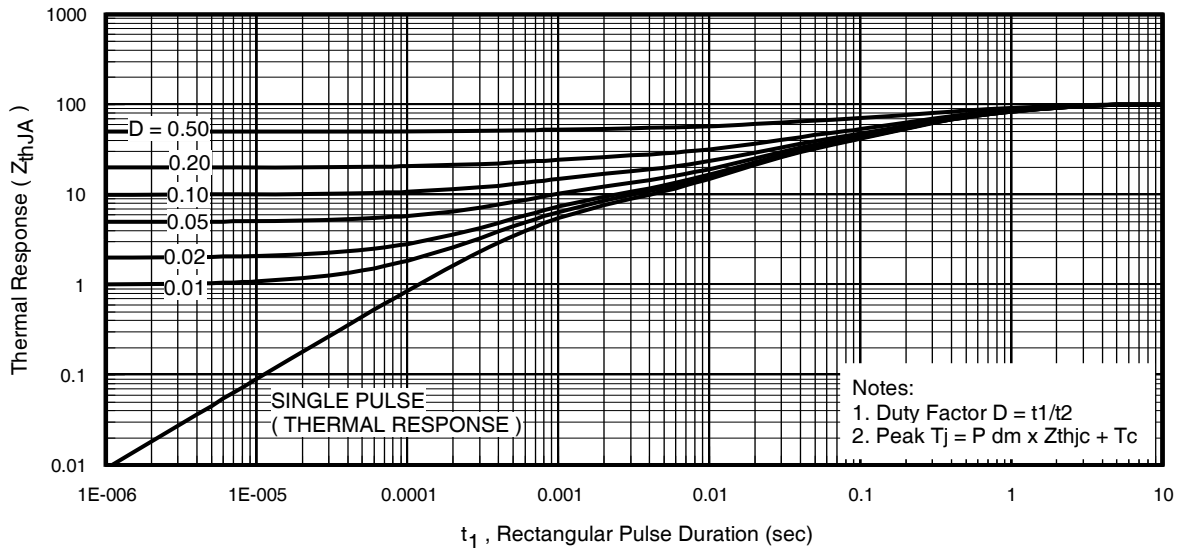


Fig 11. Typical Effective Transient Thermal Impedance, Junction-to-Ambient

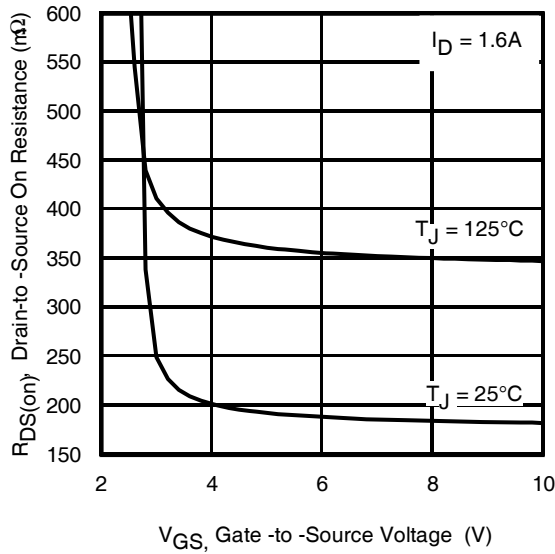


Fig 12. Typical On-Resistance Vs. Gate Voltage

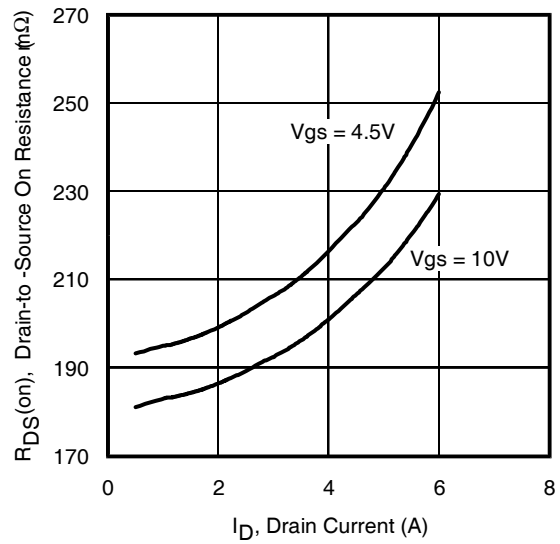


Fig 13. Typical On-Resistance Vs. Drain Current

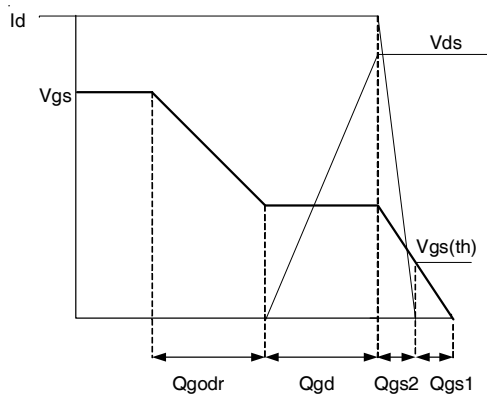


Fig 14a. Basic Gate Charge Waveform

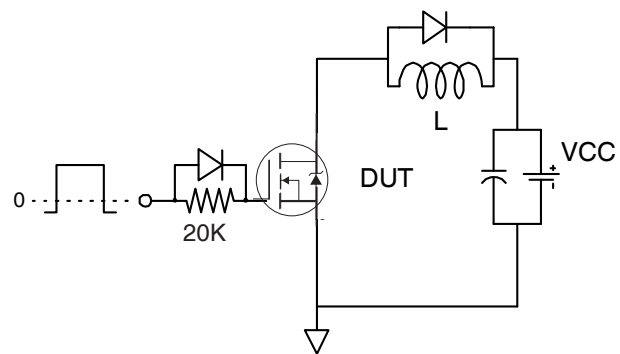


Fig 14b. Gate Charge Test Circuit

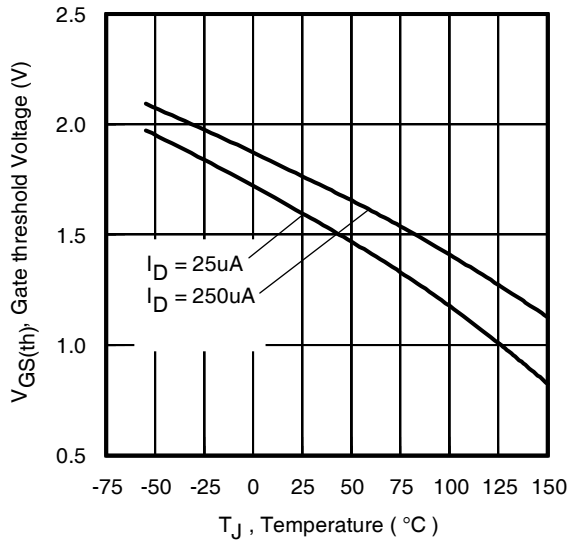


Fig 15. Typical Threshold Voltage Vs. Junction Temperature

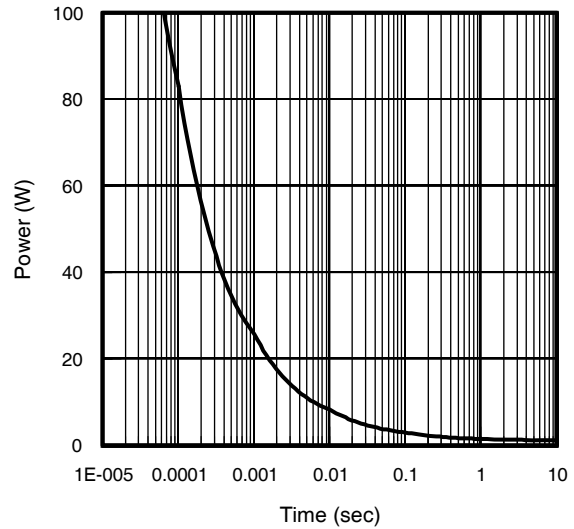


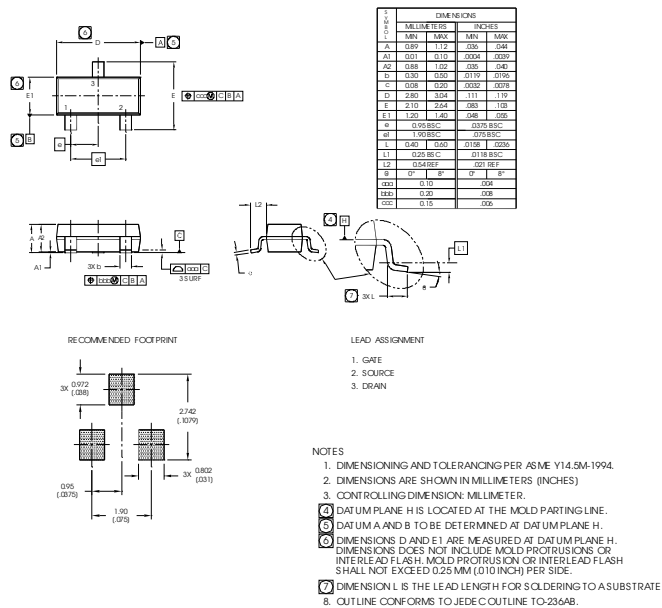
Fig 16. Typical Power Vs. Time



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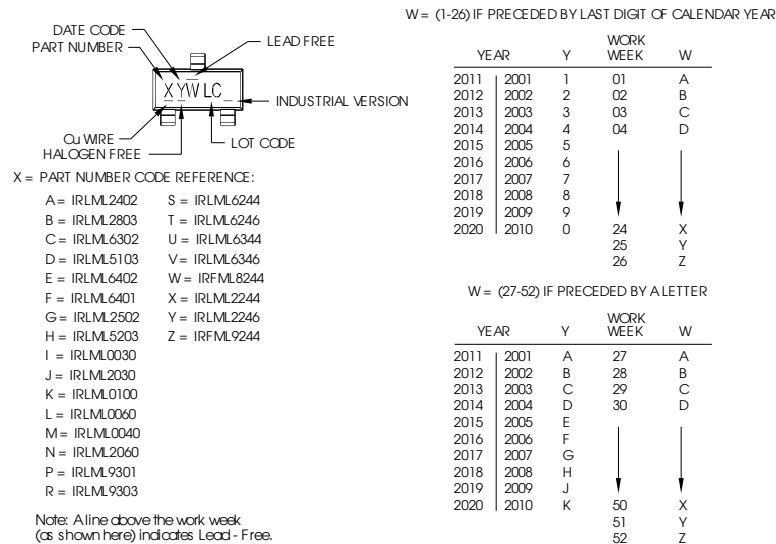
Micro3 (SOT-23) (Lead-Free) Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS			
	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.89	1.12	.036	.044
A1	0.01	0.10	.0004	.0039
A2	0.88	1.02	.035	.040
b	0.30	0.50	.0119	.0196
c	0.08	0.20	.0032	.0078
D	2.80	3.04	.111	.119
E	2.10	2.64	.083	.103
E1	1.20	1.40	.048	.055
e	0.95 BSC		.0375 BSC	
e1	1.90 BSC		.075 BSC	
L	0.40	0.60	.0158	.0236
L1	0.25 BSC		.0118 BSC	
L2	0.54 REF		.021 REF	
θ	0°	8°	0°	8°
aaa	0.10		.004	
bbb	0.20		.008	
ccc	0.15		.006	

Micro3 (SOT-23 / TO-236AB) Part Marking Information

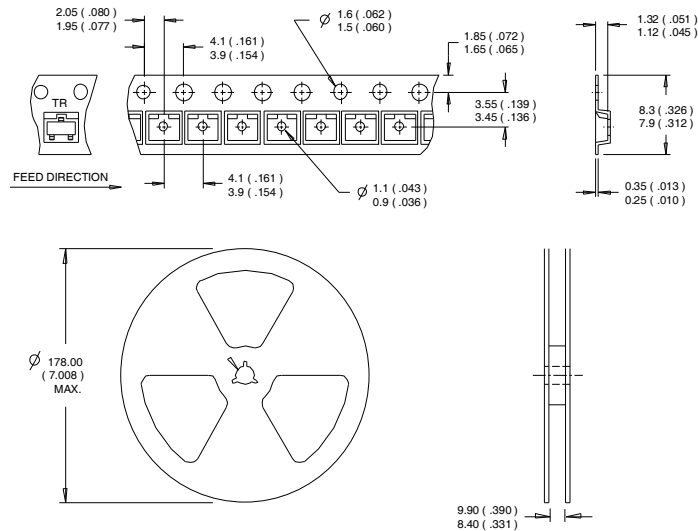
Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>



IRLML0100PbF-1

Micro3™ Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package>

Qualification information†

Qualification level	Industrial (per JEDEC JESD47F†† guidelines)	
Moisture Sensitivity Level	Micro3™ (SOT-23)	MSL1 (per JEDEC J-STD-020D††)
RoHS compliant	Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

†† Applicable version of JEDEC standard at the time of product release

Revision History

Date	Comment
10/27/2014	• Updated partmarking to reflect Industrial partmarking on page 8.

International
IR Rectifier

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To contact International Rectifier, please visit <http://www.irf.com/whoto-call/>